

Title (en)

LIGHT EMITTING DIODE HAVING SIDE REFLECTION LAYER

Title (de)

LEUCHTDIODE MIT SEITENREFLEXIONSSCHICHT

Title (fr)

DIODE ÉLECTROLUMINESCENTE À COUCHE DE RÉFLEXION LATÉRALE

Publication

EP 3364469 B1 20200708 (EN)

Application

EP 18152671 A 20180122

Priority

- KR 20170021633 A 20170217
- KR 20170024350 A 20170223
- KR 20170127323 A 20170929

Abstract (en)

[origin: EP3364469A1] Disclosed is a light emitting diode including a side reflection layer. The light emitting diode includes a substrate having a side surface; a semiconductor stack disposed under the substrate and including a first conductivity type semiconductor layer, a second conductivity type semiconductor layer, and an active layer interposed between the first conductivity type semiconductor layer and the second conductivity type semiconductor layer; an ohmic reflection layer electrically connected to the second conductivity type semiconductor layer; a first bump pad and a second bump pad disposed under the ohmic reflection layer and electrically connected to the first conductivity type semiconductor layer and the second conductivity type semiconductor layer, respectively; a side reflection layer covering the side surface of the substrate; and a capping layer covering an upper surface of the substrate and the side reflection layer.

IPC 8 full level

H01L 33/46 (2010.01)

CPC (source: CN EP KR US)

H01L 33/0075 (2013.01 - KR); **H01L 33/10** (2013.01 - CN); **H01L 33/14** (2013.01 - KR); **H01L 33/20** (2013.01 - KR US); **H01L 33/22** (2013.01 - CN); **H01L 33/44** (2013.01 - KR); **H01L 33/46** (2013.01 - EP US); **H01L 33/50** (2013.01 - CN KR); **H01L 33/505** (2013.01 - US); **H01L 33/54** (2013.01 - US); **H01L 33/60** (2013.01 - US); **H01L 33/62** (2013.01 - US); **H01L 33/382** (2013.01 - EP US)

Designated contracting state (EPC)

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DOCDB simple family (publication)

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DOCDB simple family (application)

EP 18152671 A 20180122; CN 201711275494 A 20171206; CN 201721685120 U 20171206; CN 202010360589 A 20171206; CN 202010361306 A 20171206; KR 20220053961 A 20220502; US 201815863971 A 20180107